

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:) **PATENT APPLICATION**
Inventor: Yoshi Ono)
Serial No.: Not Yet Assigned) **Attorney Docket No.**
Filed: Herewith) **SLA 0669**
Title: **LOW TEMPERATURE**
 NITRIDATION OF SILICON)
)

Honorable Commissioner for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

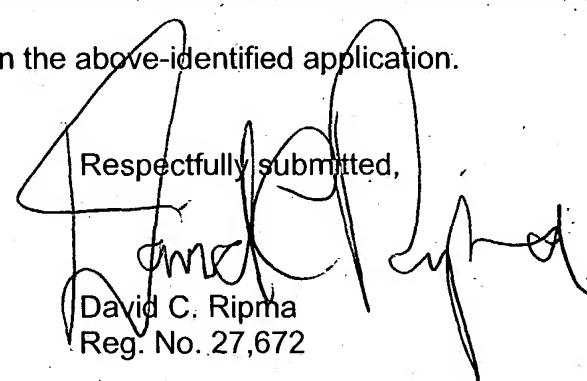
Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

(Date) 6/23/03

Respectfully submitted,


David C. Ripma
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**LIST OF PRIOR ART CITED
BY APPLICANT**

(use as many sheets as necessary)

				Complete If Known	
				Application Number	
				Filing Date	06-23-03
				First Named Inventor	Yoshi Ono
				Group Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket No.	SLA.0669

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No. ¹	U.S. Patent Document Kind Number <small>Code² (if known)</small>	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear
		6,274,510 B1	Wilk et al.	08-14-01	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵				

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	T ²
		K. Watanabe <i>et al.</i> , <i>Controlling the concentration and position of nitrogen in ultrathin oxynitride films formed by using oxygen and nitrogen radicals</i> , Appl. Phys. Lett. 76, 2940 (2000).	
		J. Joseph <i>et al.</i> , <i>A kinetics study of the electron cyclotron resonance plasma oxidation of silicon</i> , J. Vac. Sci. Technol. B10, 611 (1992).	

Examiner Signature		Date Considered	
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.1⁶ if possible. ⁶Applicant is to place a check mark here if English language Translation is attached